# IRFP350

**Vishay Siliconix** 



TO-247

**PRODUCT SUMMARY** 

V<sub>DS</sub> (V)

R<sub>DS(on)</sub> (Ω)

Q<sub>qs</sub> (nC)

Q<sub>gd</sub> (nC)

Q<sub>q</sub> (max.) (nC)

Configuration

# **Power MOSFET**

S

N-Channel MOSFET

0.30

400

150

23

80

Single

V<sub>GS</sub> = 10 V

### FEATURES

- Dynamic dV/dt rating
- · Repetitive avalanche rated
- Isolated central mounting hole
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

### DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247AC package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220AB devices. The TO-247AC is similar but superior to the earlier TO-218 package because of its isolated mounting hole. It also provides greater creepage distance between pins to meet the requirements of most safety specifications.

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free	IRFP350PbF

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V <sub>DS</sub>	400	M
Gate-source voltage			V <sub>GS</sub>	± 20	- V
		T <sub>C</sub> = 25 °C	1-	16	
Continuous drain current	VGS at TO V	T <sub>C</sub> = 100 °C	ID	10	Α
Pulsed drain current <sup>a</sup>			I <sub>DM</sub>	64	
Linear derating factor				1.5	W/°C
Single pulse avalanche energy <sup>b</sup>			E <sub>AS</sub>	390	mJ
Repetitive avalanche current <sup>a</sup>			I <sub>AR</sub>	16	А
Repetitive avalanche energy <sup>a</sup>			E <sub>AR</sub>	19	mJ
Maximum power dissipation	T <sub>C</sub> = 25 °C		PD	190	W
Peak diode recovery dV/dt <sup>c</sup>			dV/dt	4.0	V/ns
Operating junction and storage temperature range			T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Soldering recommendations (peak temperature) for 10 s				300 <sup>d</sup>	-0
Mounting torque	6.00 or M0.			10	lbf ∙ in
Mounting torque	6-32 or M3 screw			1.1	N · m

#### Notes

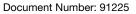
a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

b.  $V_{DD}$  = 50 V, starting T<sub>J</sub> = 25 °C, L = 2.7 mH, R<sub>g</sub>= 25  $\Omega$ , I<sub>AS</sub> = 16 A (see fig. 12)

c.  $I_{SD} \le 16 \text{ A}, \text{ dI/dt} \le 200 \text{ A/}\mu\text{s}, \text{ V}_{DD} \le \text{V}_{DS}, \text{ T}_{J} \le 150 \text{ }^\circ\text{C}$ 

d. 1.6 mm from case

S22-0051-Rev. C, 24-Jan-2022





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THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R <sub>thJA</sub>	-	40	
Case-to-sink, flat, greased surface	R <sub>thCS</sub>	0.24	-	°C/W
Maximum junction-to-case (drain)	R <sub>thJC</sub>	-	0.65	

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static		•		•		•	
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D$	= 250 μA	400	-	-	V
V <sub>DS</sub> temperature coefficient	$\Delta V_{DS}/T_{J}$	Reference to	25 °C, I <sub>D</sub> = 1 mA	-	0.51	-	V/°C
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D$	= 250 μA	2.0	-	4.0	V
Gate-source leakage	I <sub>GSS</sub>	$V_{GS} = \pm 20 V$		-	-	± 100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 400 V,		-	-	25	μA
		-	V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	250	r
Drain-source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	_	-	-	0.30	Ω
Forward transconductance	9 <sub>fs</sub>	$V_{DS} = 50 \text{ V}, \text{ I}_{DS}$	<sub>0</sub> = 9.6 A <sup>b</sup>	10	-	-	S
Dynamic				1		1	
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V,		-	2600	-	
Output capacitance	C <sub>oss</sub>	$V_{DS} = 25 V,$	<i>.</i> -	-	660	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1.0 MHz, s	see fig. 5	-	250	-	
Total gate charge	Qg			-	-	150	
Gate-source charge	Q <sub>gs</sub>	$V_{GS} = 10 V$	$I_D = 16 \text{ A}, V_{DS} = 320 \text{ V},$ see fig. 6 and 13 <sup>b</sup>	-	-	23	nC
Gate-drain charge	Q <sub>gd</sub>			-	-	80	
Turn-on delay time	t <sub>d(on)</sub>			-	16	-	
Rise time	t <sub>r</sub>	$V_{DD} = 200 V,$		-	49	-	
Turn-off delay time	t <sub>d(off)</sub>	<ul> <li>R<sub>g</sub> = 6.2 Ω, R</li> <li>see fig. 10<sup>b</sup></li> </ul>	D= 12 22	-	87	-	ns
Fall time	t <sub>f</sub>	J		-	47	-	
Internal drain inductance	L <sub>D</sub>	Between lead		-	5.0	-	
Internal source inductance	L <sub>S</sub>	6 mm (0.25") package and die contact		-	13	-	nH
Drain-Source Body Diode Characteristic	s						
Continuous source-drain diode current	I <sub>S</sub>	MOSFET sym	ibol	-	-	16	
Pulsed diode forward current <sup>a</sup>	I <sub>SM</sub>	showing the integral revers p - n junction		-	-	64	А
Body diode voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub>	= 16 A, $V_{GS}$ = 0 V <sup>b</sup>	-	-	1.6	V
Body diode reverse recovery time	t <sub>rr</sub>			-	380	570	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	$I_{\rm J} = 25 {}^{\circ}{\rm C},  I_{\rm F}$	= 16 A, dl/dt = 100 A/µs <sup>b</sup>	-	4.7	7.1	μC
Forward turn-on time	t <sub>on</sub>	Intrinsic turn-	on time is negligible (turn-or	, is domin	ated by I	and L	<u>.</u>

#### Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

b. Pulse width  $\leq$  300 µs; duty cycle  $\leq$  2 %

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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

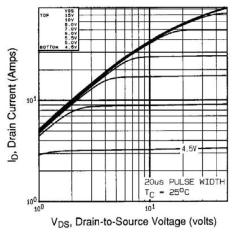


Fig. 1 - Typical Output Characteristics, T<sub>C</sub> = 25 °C

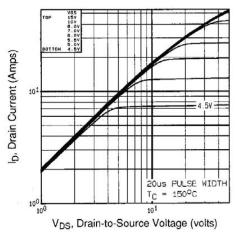


Fig. 2 - Typical Output Characteristics, T<sub>C</sub> = 150 °C

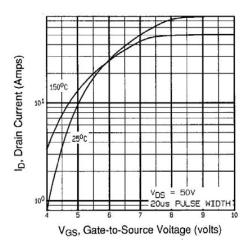


Fig. 3 - Typical Transfer Characteristics

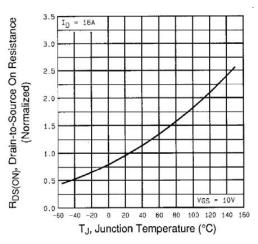


Fig. 4 - Normalized On-Resistance vs. Temperature

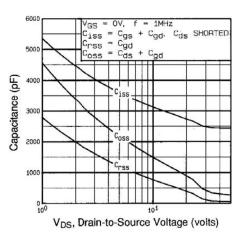


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

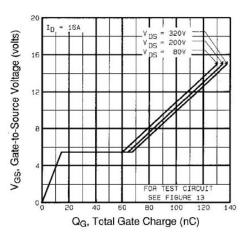


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

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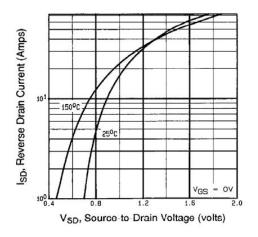


Fig. 7 - Typical Source-Drain Diode Forward Voltage

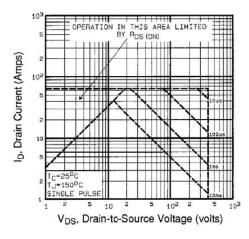


Fig. 8 - Maximum Safe Operating Area

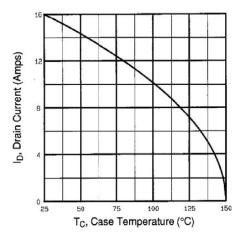


Fig. 9 - Maximum Drain Current vs. Case Temperature

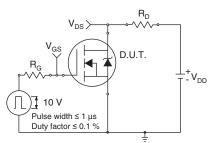


Fig. 10a - Switching Time Test Circuit

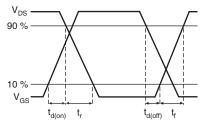


Fig. 10b - Switching Time Waveforms



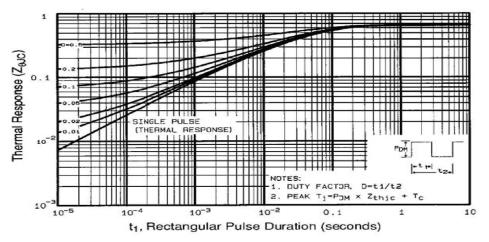


Fig. 11- Maximum Effective Transient Thermal Impedance, Junction-to-Case

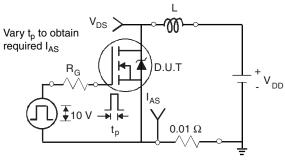


Fig. 12a - Unclamped Inductive Test Circuit

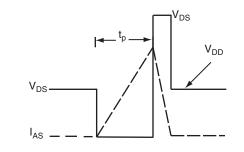


Fig. 12b - Unclamped Inductive Waveforms

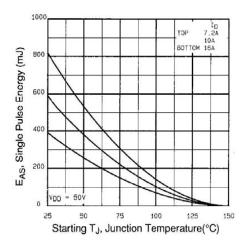
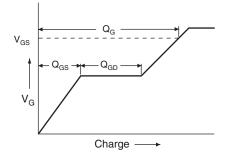


Fig. 12c - Maximum Avalanche Energy vs. Drain Current



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### Fig. 13a - Basic Gate Charge Waveform

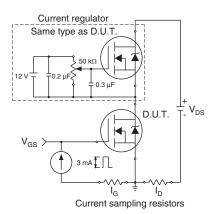
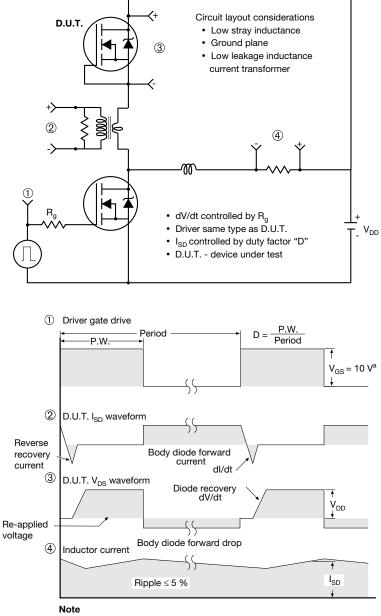


Fig. 13b - Gate Charge Test Circuit





#### Peak Diode Recovery dV/dt Test Circuit



a.  $V_{GS} = 5 V$  for logic level devices

Fig. 14 - For N-Channel

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**TO-247AC (High Voltage)** 

### VERSION 1: FACILITY CODE = 9





(	

	М	ILLIMETERS		
DIM.	MIN.	NOM.	MAX.	NOTES
А	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.17	1.27	1.37	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
С	0.40	0.50	0.60	6
c1	0.40	0.50	0.56	
D	20.40	20.55	20.70	4

		MILLIMETERS	S	
DIM.	MIN.	NOM.	MAX.	NOTES
D1	16.46	16.76	17.06	5
D2	0.56	0.66	0.76	
E	15.50	15.70	15.87	4
E1	13.46	14.02	14.16	5
E2	4.52	4.91	5.49	3
е		5.46 BSC		
L	14.90	15.15	15.40	
L1	3.96	4.06	4.16	6
ØР	3.56	3.61	3.65	7
Ø P1	7.19 ref.			
Q	5.31	5.50	5.69	
S		5.51 BSC		

### Notes

- <sup>(1)</sup> Package reference: JEDEC<sup>®</sup> TO247, variation AC
- (2) All dimensions are in mm
- <sup>(3)</sup> Slot required, notch may be rounded
- <sup>(4)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- <sup>(5)</sup> Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition



### VERSION 2: FACILITY CODE = Y



	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
A	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51	BSC	

### Notes

- <sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994
- <sup>(2)</sup> Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- <sup>(4)</sup> Thermal pad contour optional with dimensions D1 and E1
- <sup>(5)</sup> Lead finish uncontrolled in L1
- <sup>(6)</sup> Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- <sup>(7)</sup> Outline conforms to JEDEC outline TO-247 with exception of dimension c

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### VERSION 3: FACILITY CODE = N



MILLIMETERS	IETERS		MILLIMETERS		
DIM.	MIN.	MAX.	DIM.	MIN.	MAX
А	4.65	5.31	D2	0.51	1.35
A1	2.21	2.59	E	15.29	15.87
A2	1.17	1.37	E1	13.46	-
b	0.99	1.40	e	5.46	BSC
b1	0.99	1.35	k	0.:	254
b2	1.65	2.39	L	14.20	16.10
b3	1.65	2.34	L1	3.71	4.29
b4	2.59	3.43	N	7.62	BSC
b5	2.59	3.38	Р	3.56	3.66
С	0.38	0.89	P1	-	7.39
c1	0.38	0.84	Q	5.31	5.69
D	19.71	20.70	R	4.52	5.49
D1	13.08	-	S	5.51	BSC

Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994

<sup>(2)</sup> Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

<sup>(4)</sup> Thermal pad contour optional with dimensions D1 and E1

<sup>(5)</sup> Lead finish uncontrolled in L1

<sup>(6)</sup> Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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